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LEDW47-66-60

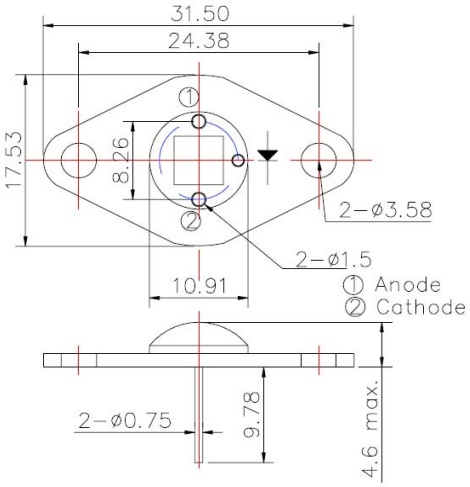
TECHNICAL DATA

High Power LED Array, 60 chips AlGaAs

LEDW47-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency InGaN diode chips, mounted on a metal stem TO-66 with AIN ceramics and covered with double coated clear silicone and epoxy resin.
This LED is designed for high operation current, and must only to be used in conjunction with proper heat sink to provide sufficient thermal conductivity!

Specifications

- Structure: AlGaAs, 60 LED chips
- Peak Wavelength: White Color
- Optical Output Power: typ. 60 mW
- Package: TO-66 stem with AIN, clear epoxy resin



(Unit: mm)

Absolute Maximum Ratings (T_C=25°C)

Item	Symbol	Value	Unit
Power Dissipation	P_D	8.5	W
Forward Current	I_F	400	mA
Pulsed Forward Current *[1]	I_{FP}	2	A
Reverse Voltage	V_R	30	V
Operating Temperature	T_{opr}	-30 … +80	°C
Storage Temperature	T_{stg}	-30 … +110	°C
Soldering Temperature *[2]	T_{sol}	260	°C

*[1] duty = 1%, pulse width = 1 µs
*[2] must be completed within 3 seconds

Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Total Radiated Power	P_O	I_F = 240 mA	-	60	-	mW
Brightness	I_V	I_F = 240 mA		13		cd
Radiant Intensity	I_E	I_F = 240 mA		35		mW/sr
Forward Voltage	V_F	I_F = 240 mA	-	19.0	-	V
Reverse Voltage	V_R	I_R = 10 µA	30	-	-	V
Viewing Half Angle	$\Theta_{1/2}$	I_F = 240 mA	-	±55	-	deg.

Heat Sink is required, thermal resistance <8K/W

Notes

- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.